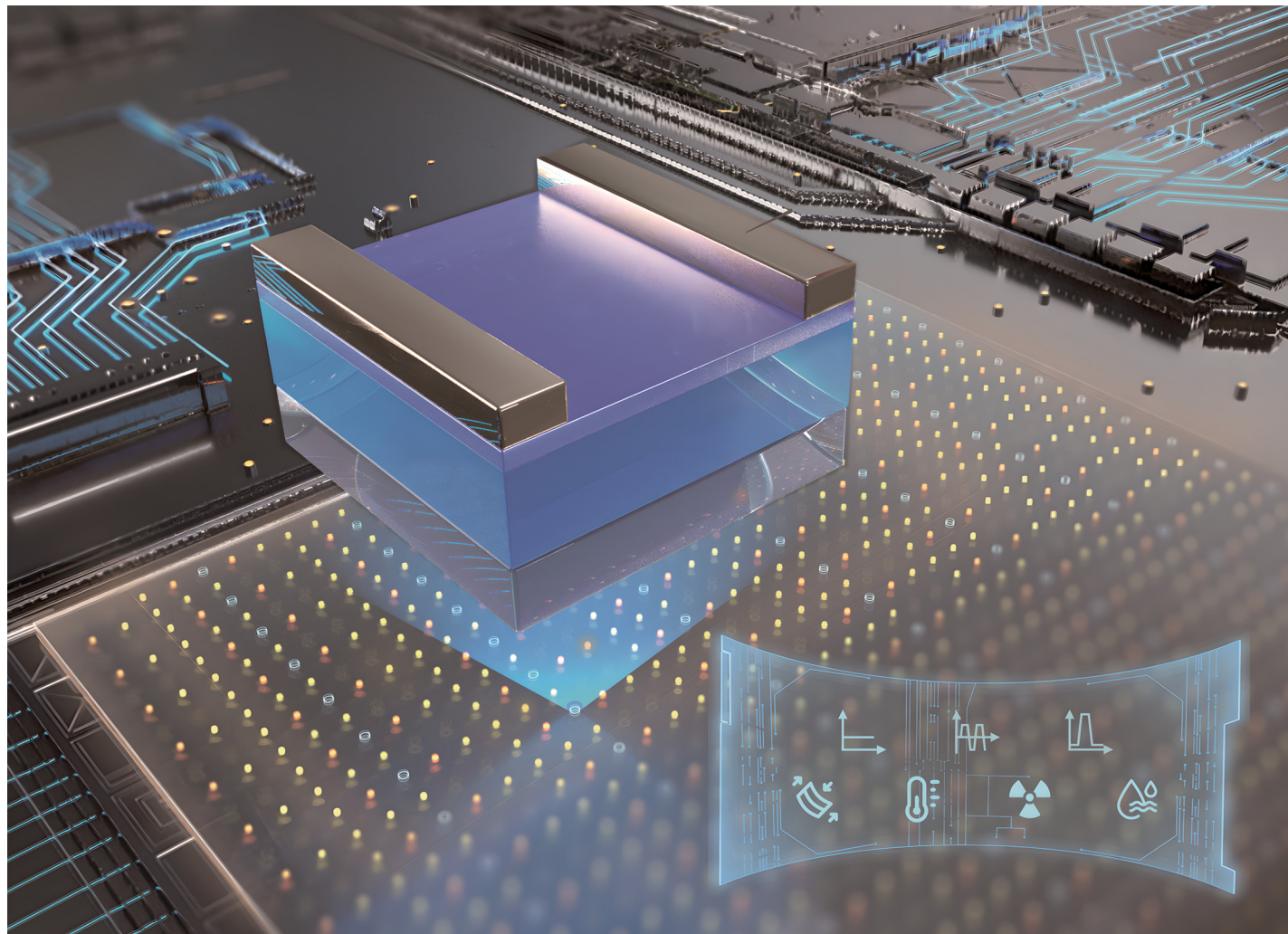


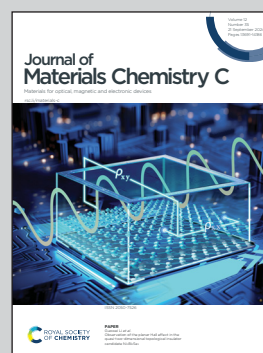


Showing a review from the State Key Laboratory of Radio Frequency Heterogeneous Integration, Shenzhen University, China

Reliability issues of amorphous oxide semiconductor-based thin film transistors

A comprehensive overview of the reliability Issues, including bias stress stability under various operation environments, electrostatic discharge reliability, bending reliability, and radiation reliability of amorphous oxide semiconductor based thin film transistors is presented, which proposes directions for future research to motivate communities to galvanize progress towards the field.

As featured in:



See Yan Yan *et al.*,
J. Mater. Chem. C, 2024, **12**, 13707.